

# C4D10120E

1200 V, 10 A Silicon Carbide Schottky Diode



TO-252-2



## Features

- 1.2 kv Schottky rectifier
- Zero reverse recovery current
- High-frequency operation
- Temperature-independent switching behavior
- Extremely fast switching
- Positive temperature coefficient on  $V_f$



Package Types: TO-252-2

PN: C4D10120

WolfSpeed, Inc. is in the process of rebranding its products and related materials pursuant to the entity name change from Cree, Inc. to WolfSpeed, Inc. During this transition period, products received may be marked with either the Cree name and/or logo or the WolfSpeed name and/or logo.

## Applications

- Solar inverters
- Switch mode power supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free wheeling diodes in inverter stages
- AC/DC converters

## Benefits

- Replace bipolar with unipolar rectifiers
- Essentially no switching losses
- Higher efficiency
- Reduction of heat sink requirements
- Parallel devices without thermal runaway

## Maximum Ratings ( $T_c = 25\text{ }^\circ\text{C}$ Unless Otherwise Specified)

Parameter	Symbol	Value	Unit	Test Conditions	Note
Repetitive Peak Reverse Voltage	$V_{RRM}$	1200	V		
Surge Peak Reverse Voltage	$V_{RSM}$	1300			
DC Blocking Voltage	$V_{DC}$	1200			
Continuous Forward Current	$I_F$	33	A	$T_c = 25\text{ }^\circ\text{C}$	Fig. 3
		16		$T_c = 135\text{ }^\circ\text{C}$	
		10		$T_c = 156\text{ }^\circ\text{C}$	
Repetitive Peak Forward Surge Current	$I_{FRM}$	47	A	$T_c = 25\text{ }^\circ\text{C}$ , $t_p = 10\text{ ms}$ , Half Sine Pulse	
		31.5		$T_c = 110\text{ }^\circ\text{C}$ , $t_p = 10\text{ ms}$ , Half Sine Pulse	
Non-Repetitive Peak Forward Surge Current	$I_{FSM}$	71	A	$T_c = 25\text{ }^\circ\text{C}$ , $t_p = 10\text{ ms}$ , Half Sine Pulse	Fig. 8
		59		$T_c = 110\text{ }^\circ\text{C}$ , $t_p = 10\text{ ms}$ , Half Sine Pulse	
Non-Repetitive Peak Forward Current	$I_{F,Max}$	750	A	$T_c = 25\text{ }^\circ\text{C}$ , $t_p = 10\text{ }\mu\text{s}$ , Pulse	Fig. 8
		620		$T_c = 110\text{ }^\circ\text{C}$ , $t_p = 10\text{ }\mu\text{s}$ , Pulse	
Power Dissipation	$P_{tot}$	166.5	W	$T_c = 25\text{ }^\circ\text{C}$	Fig. 4
		72		$T_c = 110\text{ }^\circ\text{C}$	
Diode $dV/dt$ Ruggedness	$dV/dt$	200	V/ns	$V_R = 0\text{--}960\text{ V}$	
$i^2t$ Value	$\int i^2 dt$	25	$A^2s$	$T_c = 25\text{ }^\circ\text{C}$ , $t_p = 10\text{ ms}$	
		17.5		$T_c = 110\text{ }^\circ\text{C}$ , $t_p = 10\text{ ms}$	
Operating Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +175	$^\circ\text{C}$		



## Electrical Characteristics

Parameter	Symbol	Typ.	Max.	Unit	Test Conditions	Note
Forward Voltage	$V_F$	1.5	1.8	V	$I_F = 10 \text{ A}, T_J = 25^\circ\text{C}$	Fig. 1
		2.2	3		$I_F = 10 \text{ A}, T_J = 175^\circ\text{C}$	
Reverse Current	$I_R$	30	250	$\mu\text{A}$	$V_R = 1200 \text{ V}, T_J = 25^\circ\text{C}$	Fig. 2
		55	350		$V_R = 1200 \text{ V}, T_J = 175^\circ\text{C}$	
Total Capacitive Charge	$Q_C$	52		nC	$V_R = 800 \text{ V}, I_F = 10 \text{ A}$ $di/dt = 200 \text{ A}/\mu\text{S}$ $T_J = 25^\circ\text{C}$	Fig. 5
Total Capacitance	C	754		pF	$V_R = 0 \text{ V}, T_J = 25^\circ\text{C}, f = 1 \text{ MHz}$	Fig. 6
		45			$V_R = 400 \text{ V}, T_J = 25^\circ\text{C}, f = 1 \text{ MHz}$	
		38			$V_R = 800 \text{ V}, T_J = 25^\circ\text{C}, f = 1 \text{ MHz}$	
Capacitance Stored Energy	$E_C$	14.5		$\mu\text{J}$	$V_R = 800 \text{ V}$	Fig. 7

Note: This is a majority carrier diode, so there is no reverse recovery charge.

## Thermal Characteristics

Parameter	Symbol	Typ.	Unit	Note
Thermal Resistance from Junction to Case	$R_{\theta JC}$	0.9	$^\circ\text{C}/\text{W}$	Fig. 9

## Typical Performance

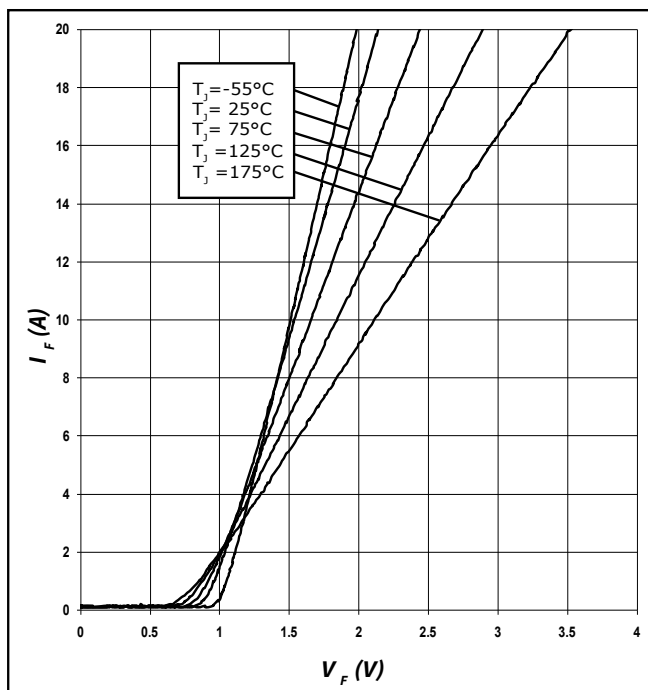


Figure 1. Forward Characteristics

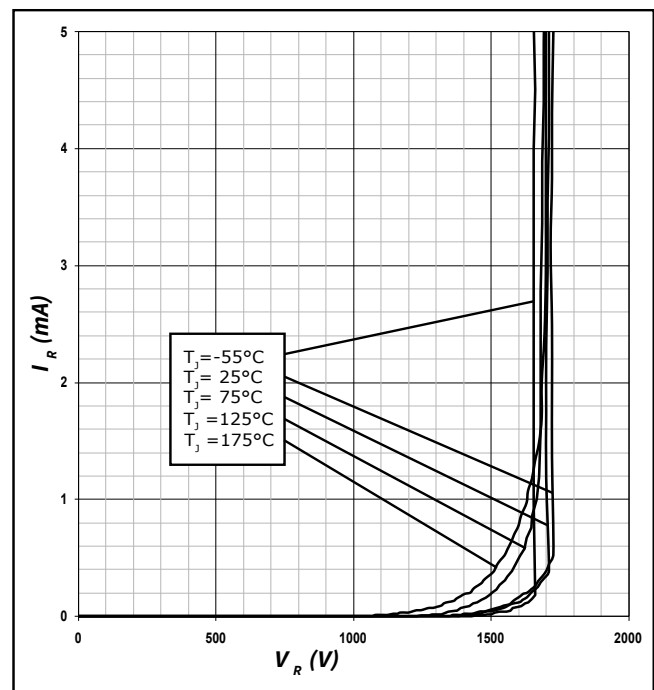


Figure 2. Reverse Characteristics



Typical Performance

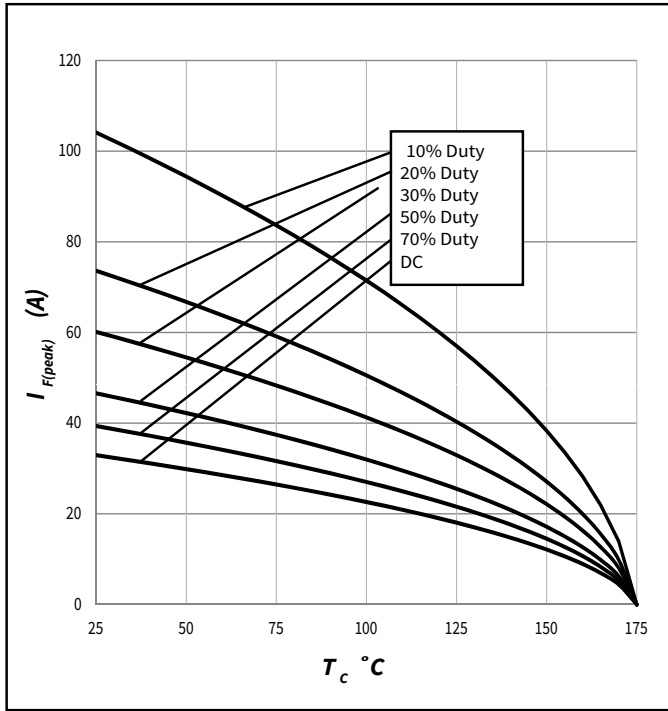


Figure 3. Current Derating

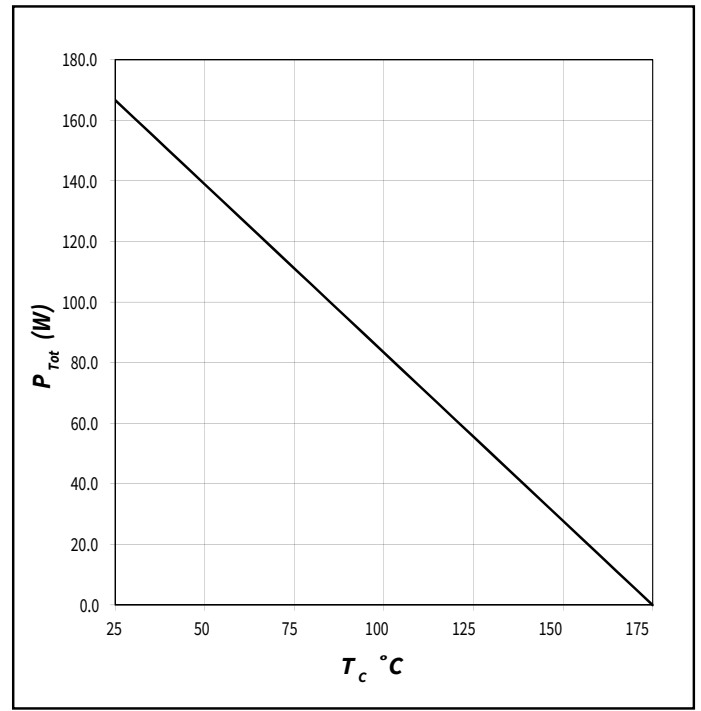


Figure 4. Power Derating

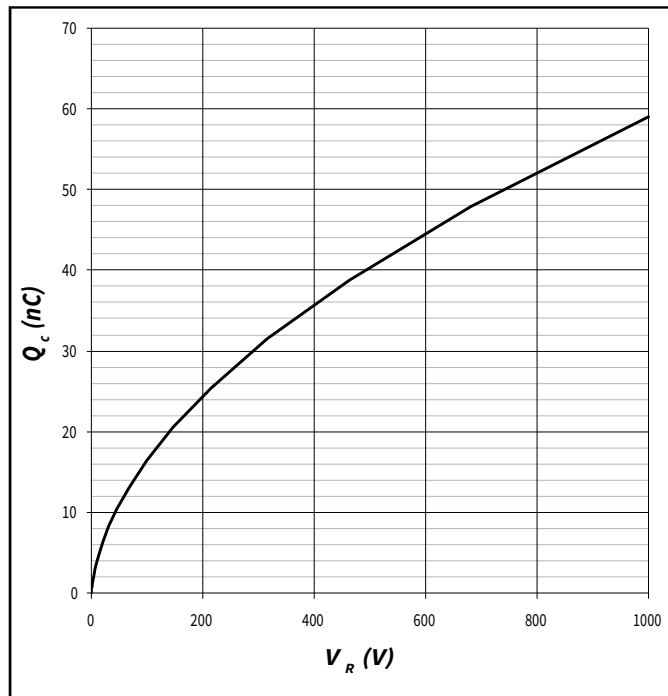


Figure 5. Recovery Charge vs. Reverse Voltage

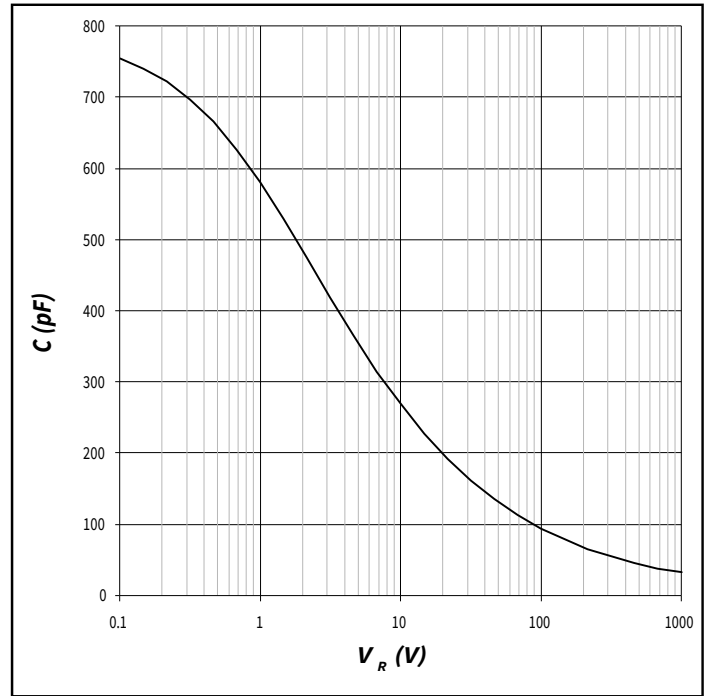


Figure 6. Capacitance vs. Reverse Voltage



Typical Performance

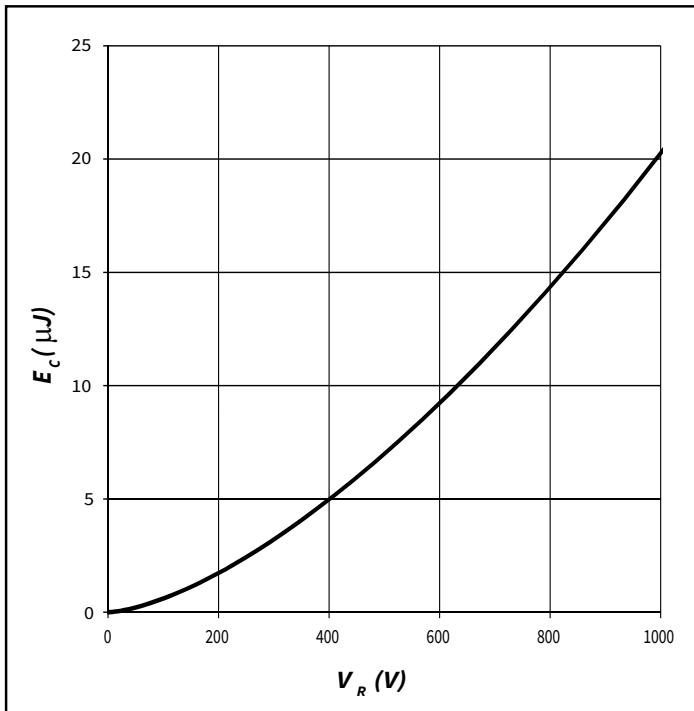


Figure 7. Typical Capacitance Stored Energy

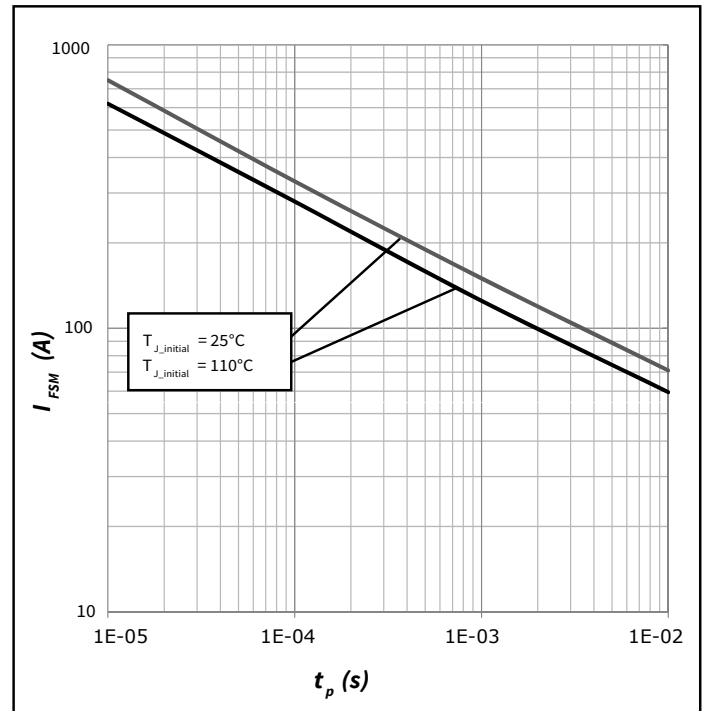


Figure 8. Non-Repetitive Peak Forward Surge Current Versus Pulse Duration (Sinusoidal Waveform)

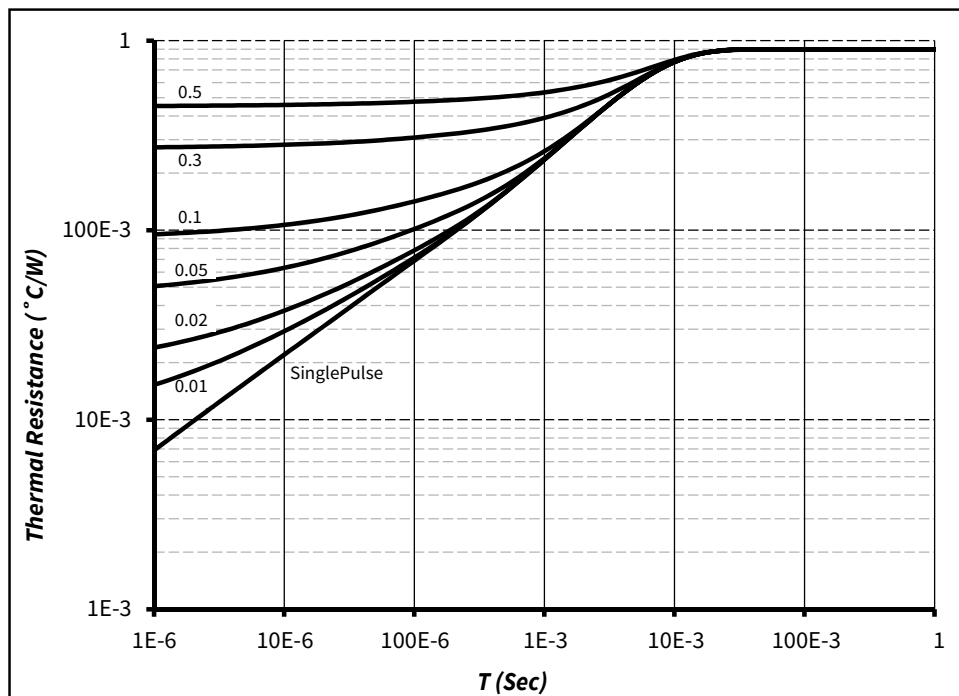
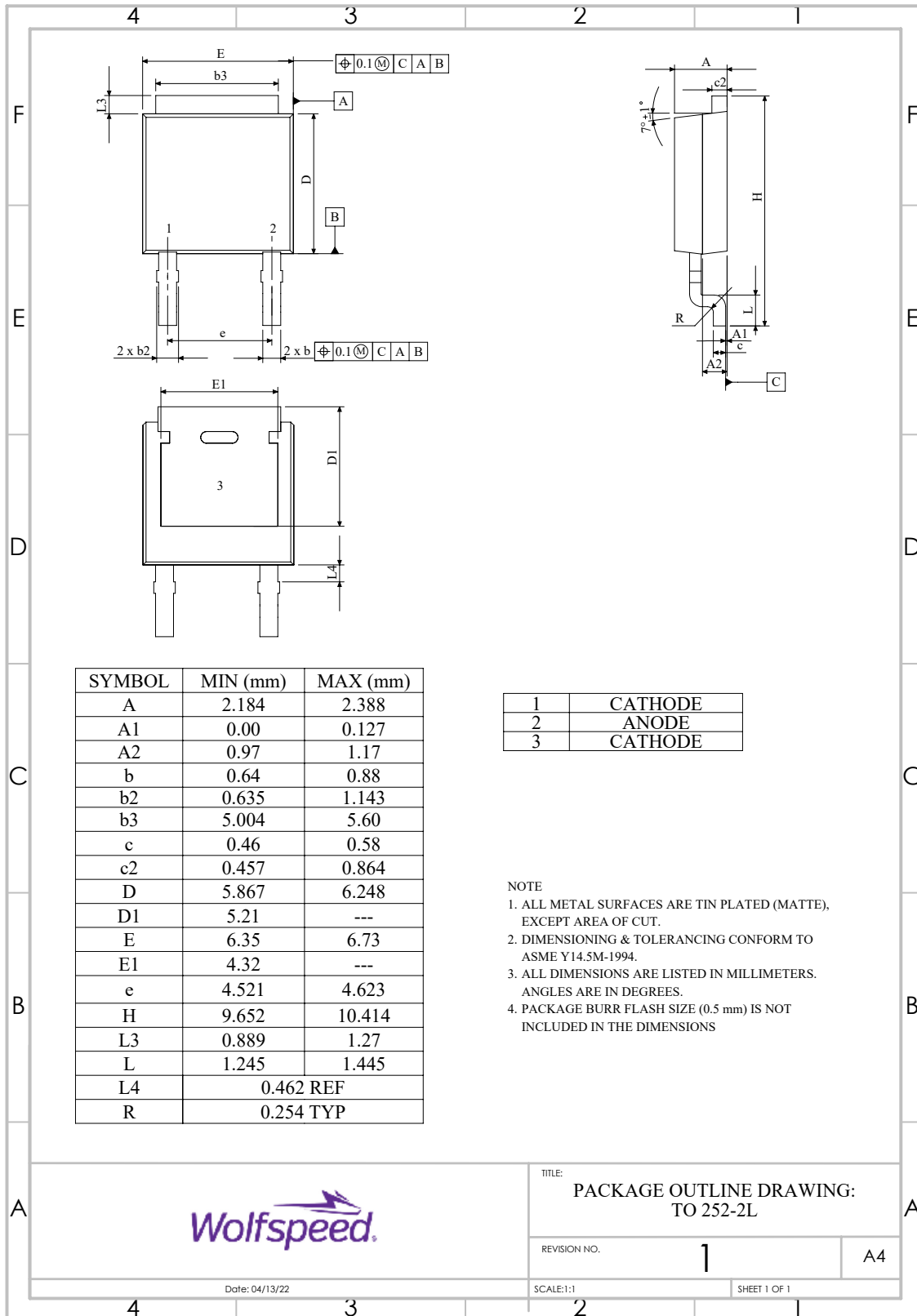


Figure 9. Transient Thermal Impedance



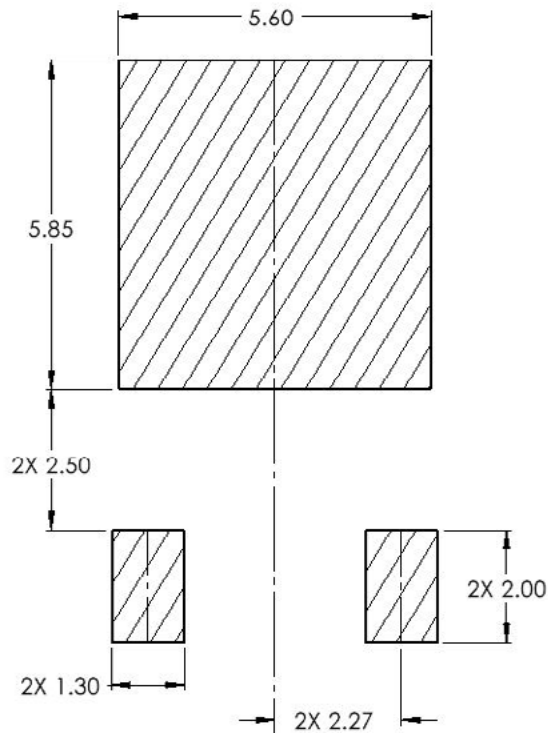
### Package Dimensions

Package: TO-252-2



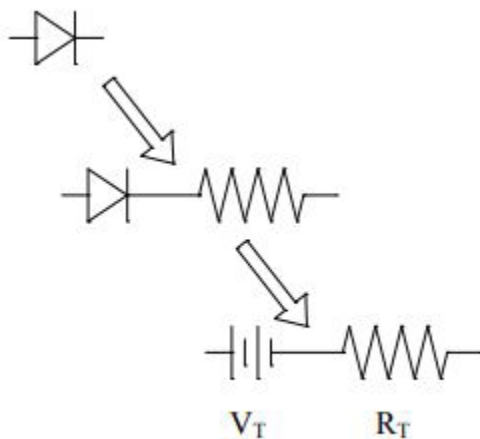


## Recommended Solder Pad Layout



Part Number	Package	Marking
C4D10120E	TO-252-2	C4D10120

## Diode Model



$$V_{FT} = V_T + I_f * R_T$$

$$V_T = 0.98 + (T_j * -1.71 * 10^{-3})$$

$$R_T = 0.040 + (T_j * 5.32 * 10^{-4})$$

**Note:**  $T_j$  = Diode Junction Temperature In Degrees Celsius, valid from 25°C to 175°C



## Revision History

Current Revision	Date of Release	Description of Changes
9	September-2023	Updated Wolfspeed branding, package drawing, and solder pad layout
10	October-2023	Corrected solder pad layout and diode model



## Notes & Disclaimer

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